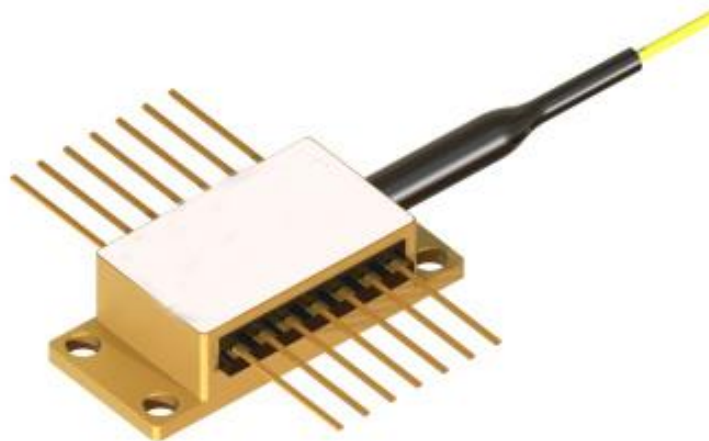


1000nm 25mW SLD Laser Diode



● Product Description

Superluminescent diodes (SLDs) are semiconductor optoelectronic devices intermediate between lasers (LDs) and light-emitting diodes (LEDs). Similar to laser diodes, SLDs are based on electrically driven PN junctions, which exhibit optical activity under forward bias and produce amplified spontaneous emission over a wide wavelength range. The peak wavelength and intensity of an SLD depend on the composition of the active material and the level of injected current. SLDs are designed to provide high single-pass gain for spontaneous emission generated along the waveguide, but unlike laser diodes, the feedback is insufficient to achieve lasing action.

● Product features

Broad spectrum; Low coherence; High output power; Fiber-coupled design;

High output stability

● Part Number

MP-SLD-1000-25-14BF-PA

● Application area

Optical Coherence Tomography (OCT) | Distributed Fiber-optic Sensing

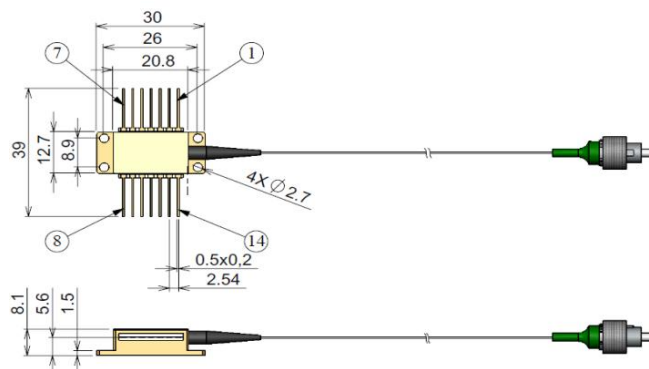
(DAS/DTS) | Fiber-optic Gyroscopes (FOG) | Quantum Optics | WDM System

Verification

● Core parameters

Average Wavelength	Spectral Width (FWHM)	Output Power
1000 nm	3MHz	25 mW

● Dimension Drawing



Pin identification:

- 1 TEC "+"
- 2 Thermistor
- 3 -
- 4 -
- 5 Thermistor
- 6 -
- 7 -
- 8 -
- 9 -
- 10 SLD anode "+"
- 11 SLD cathode "-"
- 12 -
- 13 Case
- 14 TEC "-"



● General Parameters

Detailed parameters

Specifications:					
Test conditions: continuous operation, chip temperature 25°C, case installed on room temperature heat sink					
Parameters	Symb ols	Minim um	Typical values	Maxi mum	unit
Operating output power	P _{out}	15	25		mW
Average wavelength	λ_m	985	1000	1015	nm
Bandwidth @ -3dB	$\Delta\lambda$	80	100		nm
Spectral inclination amplitude			1	3	dB
The maximum position of the ground state	λ_g	1015	1030	1045	nm
The maximum position of the excited state	λ_e	940	955	970	nm
ASE Spectral Ripple*			0.02	0.3	dB
Polarization extinction ratio	PER	15	20		dB
Operating current	I _{op}		600	700	mA
Forward voltage	V _f		1.7	1.9	V

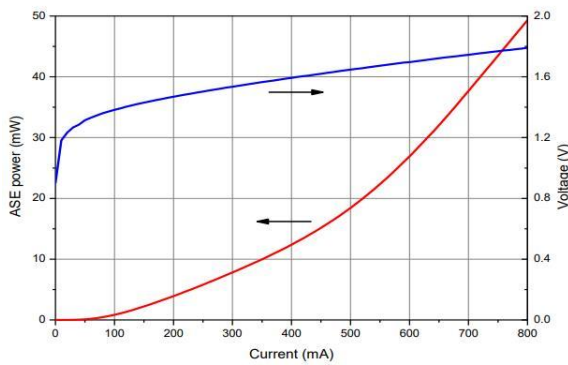


Rising time	Trise	0.15	ns
Drop time	Tfall	0.5	ns

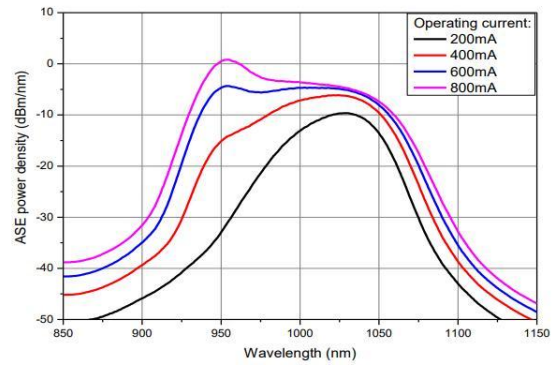
* RMS in the 1nm range at ASE max, 10pm resolution

Typical performance is for reference only

Light-Current-Voltage Characteristics



Spectral Characteristics



Wavelength power density curve

Innolume SLD ASE spectra

